

Silicon NPN Power Transistors

BUV70

DESCRIPTION

- With TO-3PN package
- High breakdown voltage
- Fast switching speed
- Wide area of safe operation

APPLICATIONS

- For switching regulator applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

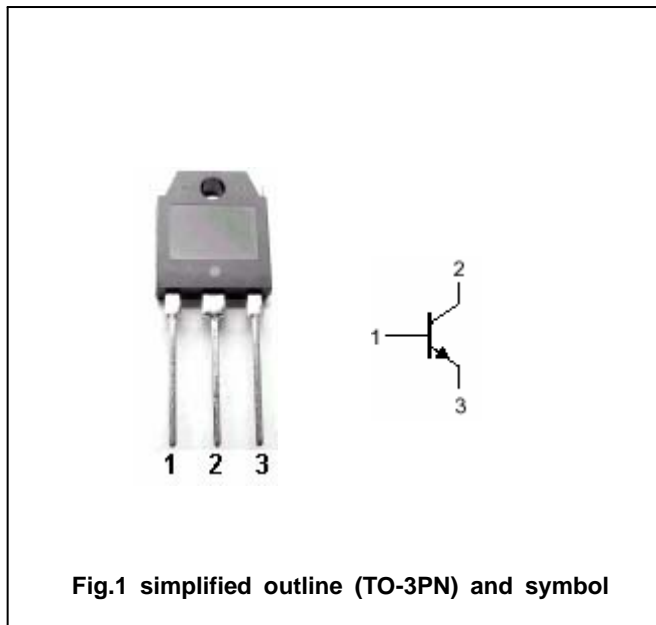


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25 )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	1300	V
$V_{CEO}$	Collector-emitter voltage	Open base	550	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current		10	A
$I_B$	Base current		4	A
$P_C$	Collector power dissipation	$T_C=25$	140	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## BUV70

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =5mA ; I <sub>B</sub> =0	550			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =6A; I <sub>B</sub> =1.2A			2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =6A; I <sub>B</sub> =1.2A			1.5	V
I <sub>CB0</sub>	Collector cut-off current	V <sub>CB</sub> =500V; I <sub>E</sub> =0			10	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =3.2A ; V <sub>CE</sub> =2V	5			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =10V		9		MHz

固电半导体

INCHANGE SEMICONDUCTOR

PACKAGE OUTLINE

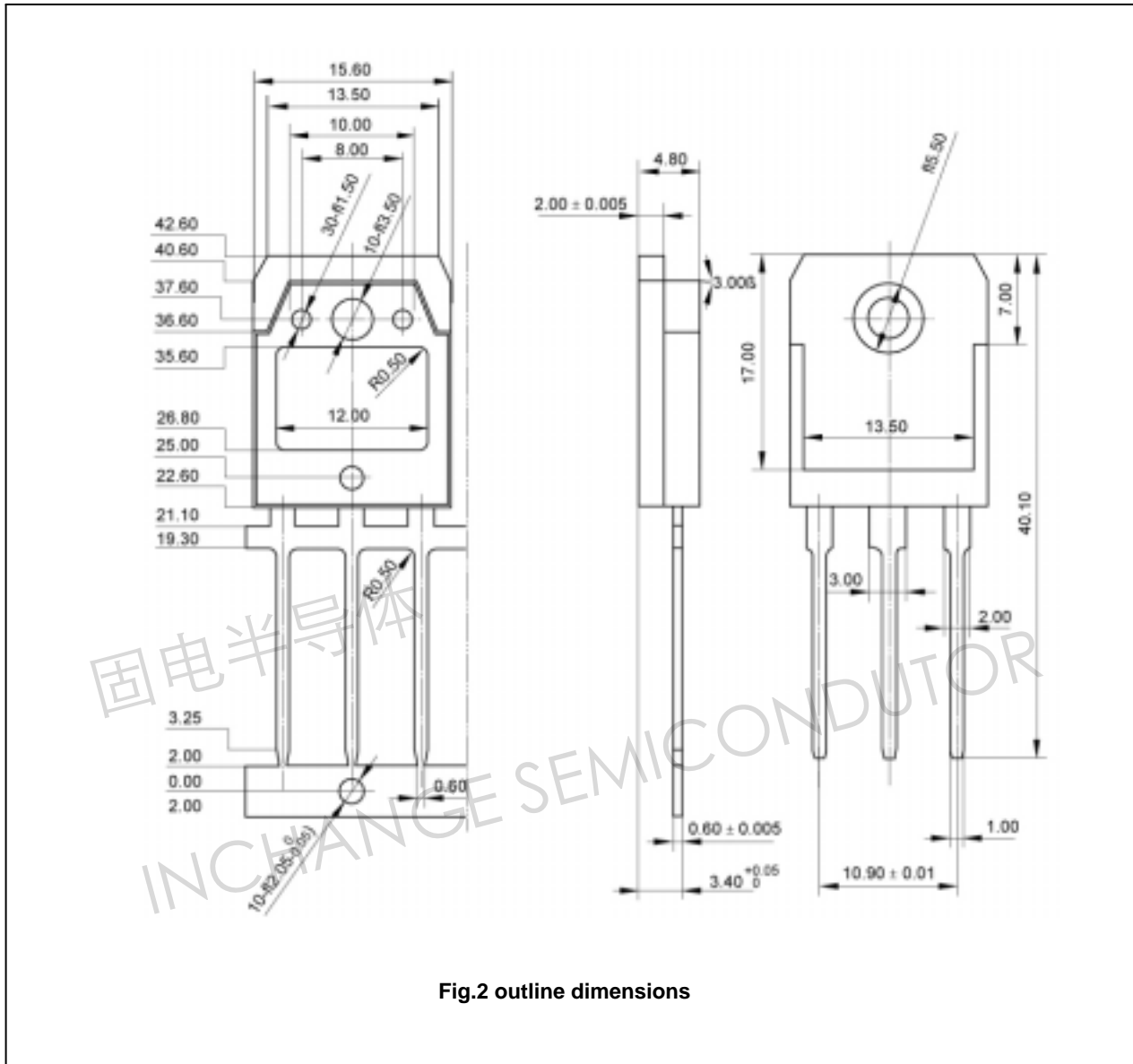


Fig.2 outline dimensions